

Metal Assisted Chemical Etching for Silicon Nanowires Formation

In this work the silicon nanopillars were produced by means of metal assisted chemical etching in two stages. It was determined that using the amount of AgNO₃ of 68 mg in the first solution and the duration of the first stage of 20 sec made possible to reduce the sunlight reflection of silicon substrate from 20-30% to 10-12%.

Primary author: Mr KULISH, Dmytro

Presenter: Mr KULISH, Dmytro

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